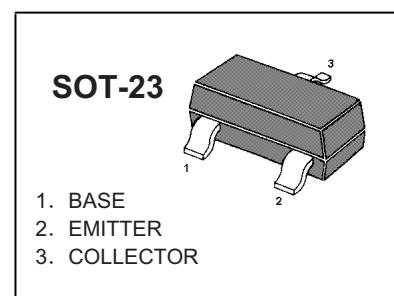


MMBT5401 TRANSISTOR (PNP)

FEATURES

Complementary to MMBT5551

Ideal for medium power amplification and switching



MARKING: 2L

MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55-150	$^\circ C$

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -120 V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$		-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -5V, I_C = -1mA$	80		
	h_{FE2}	$V_{CE} = -5V, I_C = -10mA$	100	300	
	h_{FE3}	$V_{CE} = -5V, I_C = -50mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 mA, I_B = -5mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50 mA, I_B = -5mA$		-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$	100		MHz

Typical Characteristics

MMBT5401

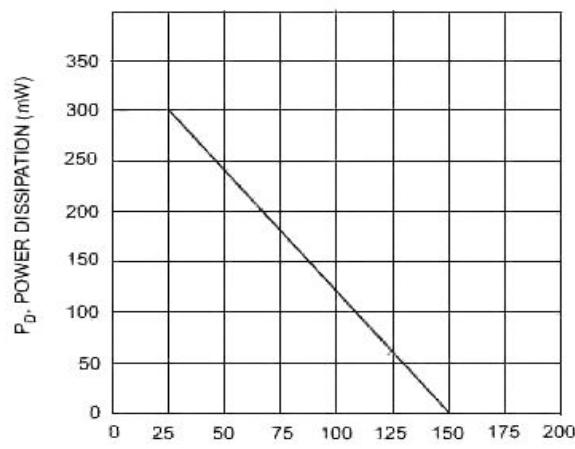


Fig. 1. Max Power Dissipation vs.
Ambient Temperature

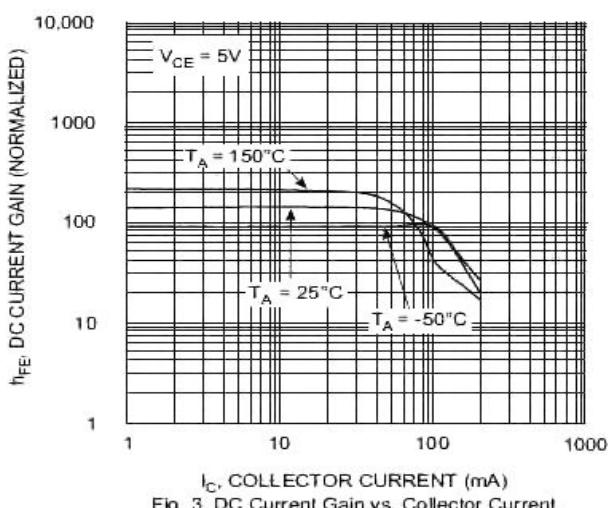


Fig. 3. DC Current Gain vs. Collector Current

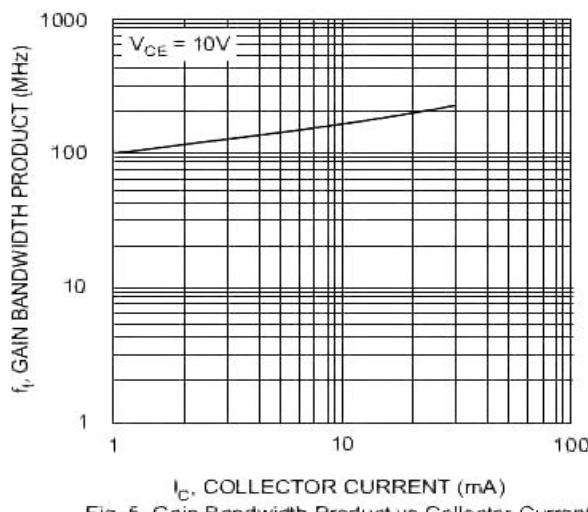


Fig. 5. Gain Bandwidth Product vs. Collector Current

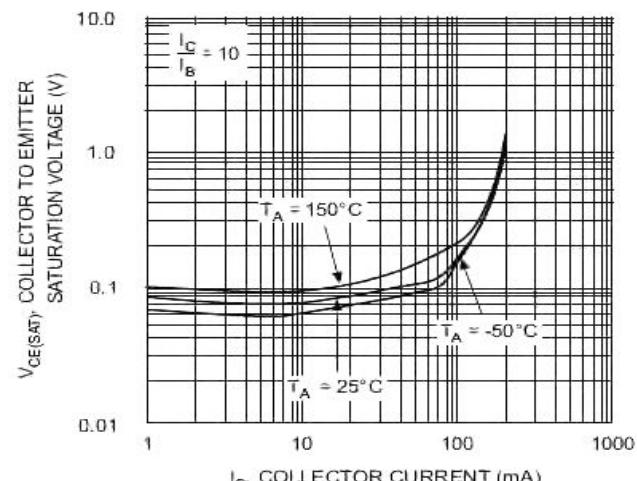


Fig. 2. Collector Emitter Saturation Voltage
vs. Collector Current

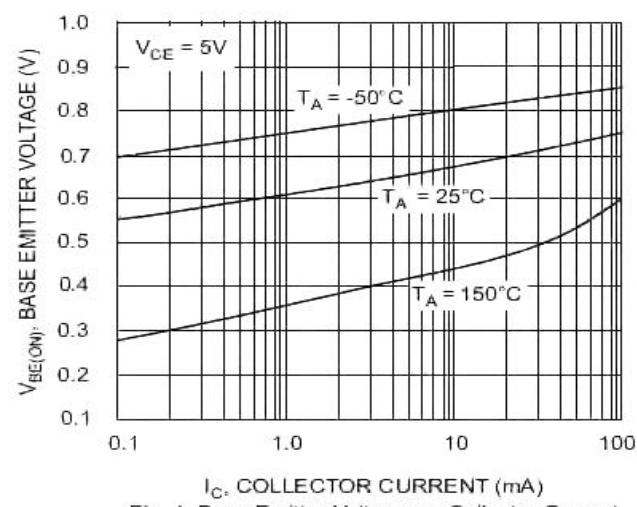
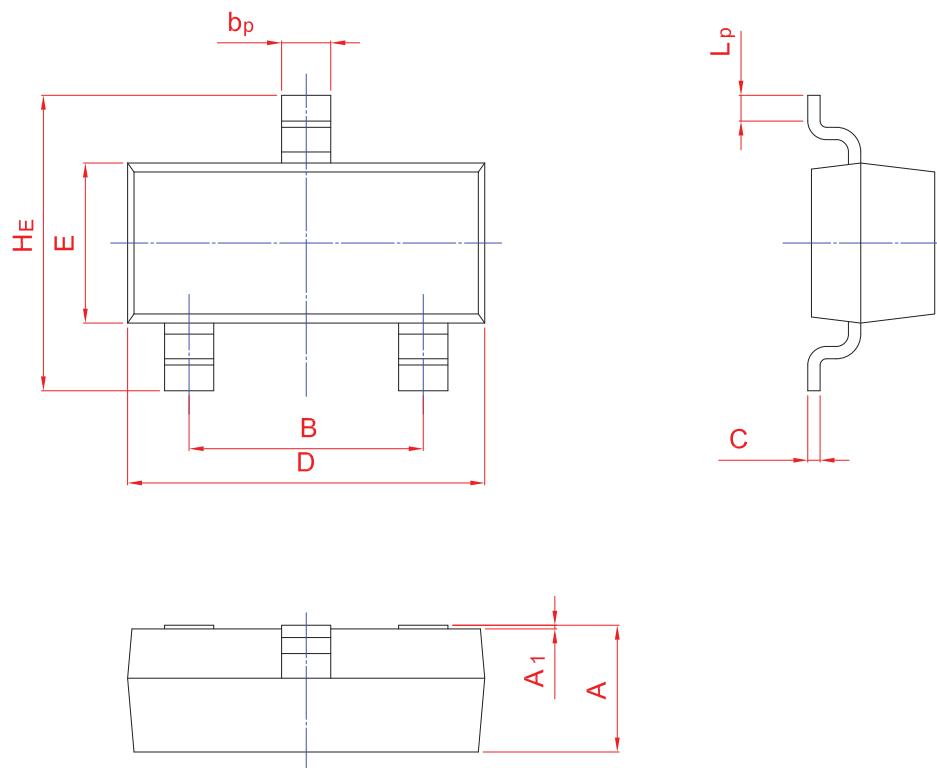


Fig. 4. Base Emitter Voltage vs. Collector Current

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20